











TL081, TL081A, TL081B, TL082, TL082A TL082B, TL084, TL084A, TL084B

SLOS081I-FEBRUARY 1977-REVISED MAY 2015

TL08xx JFET-Input Operational Amplifiers

Features

- Low Power Consumption: 1.4 mA/ch Typical
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias Current: 30 pA Typical
- Low Input Offset Current: 5 pA Typical
- **Output Short-Circuit Protection**
- Low Total Harmonic Distortion: 0.003% Typical
- High Input Impedance: JFET Input Stage
- Latch-Up-Free Operation
- High Slew Rate: 13 V/µs Typical
- Common-Mode Input Voltage Range Includes V_{CC+}

Applications

- **Tablets**
- White goods
- Personal electronics
- Computers

3 Description

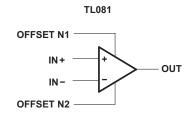
The TL08xx JFET-input operational amplifier family is designed to offer a wider selection than any previously developed operational amplifier family. Each of these JFET-input operational amplifiers incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low input bias offset currents, and low offset-voltage temperature coefficient.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TL084xD	SOIC (14)	8.65 mm × 3.91 mm
TL08xxFK	LCCC (20)	8.89 mm × 8.89 mm
TL084xJ	CDIP (14)	19.56 mm × 6.92 mm
TL084xN	PDIP (14)	19.3 mm × 6.35 mm
TL084xNS	SO (14)	10.3 mm × 5.3 mm
TL084xPW	TSSOP (14)	5.0 mm × 4.4 mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

Schematic Symbol



TL082 (EACH AMPLIFIER) TL084 (EACH AMPLIFIER)

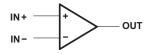




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (January 2014) to Revision I

Page

Added Pin Configuration and Functions section, Storage Conditions table, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section
 Added Applications
 Moved Typical Characteristics into Specifications section

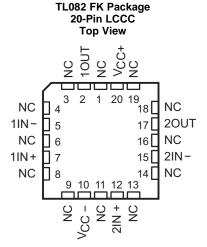
Changes from Revision G (September 2004) to Revision H

Page

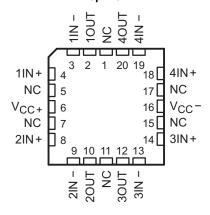
Updated document to new TI data sheet format - no specification changes.
 Deleted Ordering Information table.



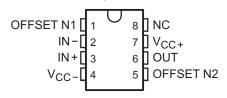
5 Pin Configuration and Functions



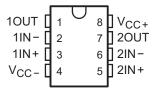
TL084 FK Package 20-Pin LCCC Top View



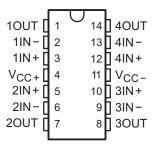
TL081 and TL081x D, P, and PS Package 8-Pin SOIC, PDIP, and SO Top View



TL082 and TL082x D, JG, P, PS and PW Package 8-Pin SOIC, CDIP, PDIP, SO, and TSSOP Top View



TL084 and TL084x D, J, N, NS and PW Package 14-Pin SOIC, CDIP, PDIP, SO, and TSSOP Top View



Pin Functions

		PII	N				
	TL081	TLO	082	TL	084		
NAME	SOIC, PDIP, SO	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	I/O	DESCRIPTION
1IN-	_	2	5	2	3	1	Negative input
1IN+	_	3	7	3	4	- 1	Positive input
1OUT	_	1	2	1	2	0	Output
2IN-	_	6	15	6	9	I	Negative input
2IN+	_	5	12	5	8	I	Positive input
2OUT	_	7	17	7	10	0	Output
3IN-	_	_	_	9	13	1	Negative input
3IN+	_	_	_	10	14	ı	Positive input
3OUT	_	_	_	8	12	0	Output
4IN-	_	_	_	13	19	I	Negative input
4IN+	_	_	_	12	18	I	Positive input
4OUT	_	_		14	20	0	Output



Pin Functions (continued)

		PII	N										
	TL081	TLO	082	TL	.084								
NAME	SOIC, PDIP, SO	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	I/O	DESCRIPTION						
IN-	2	_	_	_	_	I	Negative input						
IN+	3	_	ĺ		I	I	Positive input						
			1 3		1								
			4 6	_	-	-					5		
NC	8	_	8 9	_	7	_	Do not connect						
			11 13		11								
			14 16		15								
			18		17								
OFFSET N1	1		l		— — Input offset adjustment		Input offset adjustment		Input offset adjustment				
OFFSET N2	5	_	_	_	_	_	Input offset adjustment						
OUT	6	_				0	Output						
V _{CC} -	4	4	10	11	16	_	Power supply						
V _{CC+}	7	8	20	4	6	_	Power supply						



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

					MIN	MAX	UNIT
V _{CC+}	Supply voltage (2)					18	V
V _{CC} -	Supply voltage ⁽²⁾					-18	V
V _{ID}	Differential input voltage (3)					±30	V
VI	Input voltage (2)(4)					±15	V
	Duration of output short circuit (5)				Unlin	nited	
	Continuous total power dissipation			S	ee Dissipatio	n Rating Table	
			TL08_C TL08_AC TL08_BC		0	70	
T _A	Operating free-air temperature		TL08_I		-40	85	°C
			TL084Q		-40	125	
			TL08_M		- 55	125	
	Operating virtual junction temperat	ure				150	ô
T _C	Case temperature for 60 seconds	FK package	TL08_M			260	°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	J or JG package	TL08_M			300	°C
T _{stg}	Storage temperature				-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) All voltage values, except differential voltages, are with respect to the midpoint between V_{CC-} and V_{CC-}
- (3) Differential voltages are at IN+, with respect to IN-.
- (4) The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
- (5) The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	1000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	1500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	,	MIN	MAX	UNIT
Supply voltage		5	15	V
Supply voltage		-5	-15	V
Common-mode voltage		V _{CC} - + 4	V _{CC+} – 4	V
	TL08xM	-55	125	
A self-te at the search and	TL08xQ	-40	125	00
Ambient temperature	TL08xl	-40	85	°C
	TL08xC	0	70	
	Supply voltage Supply voltage	Supply voltage Supply voltage Common-mode voltage TL08xM TL08xQ TL08xI	MIN Supply voltage 5 Supply voltage -5 Common-mode voltage V _{CC} + 4 TL08xM -55 TL08xQ -40 TL08xI -40	MIN MAX Supply voltage 5 15 Supply voltage -5 -15 Common-mode voltage V _{CC+} + 4 V _{CC+} - 4 Ambient temperature TL08xM -55 125 TL08xQ -40 125 TL08xI -40 85

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⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

			TL08xx									
	(4)	D (SOIC)		N (PDIP)	NS (SO) P (PDIP)		PS (SO)	PW (TSSOP)				
THERMAL METRIC ⁽¹⁾		8 PINS	14 PINS	14 PINS	14 PINS	{PIN COUNT} PINS	{PIN COUNT} PINS	8 PINS	14 PINS	UNIT		
$R_{\theta JA}$	Junction-to-ambient thermal resistance (2)(3)	97	86	76	80	85	95	149	113	°C/W		

- For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.
- Maximum power dissipation is a function of $T_{J(max)}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_{J(max)} T_A) / R_{\theta JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability. The package thermal impedance is calculated in accordance with JESD 51-7.

6.5 Electrical Characteristics for TL08xC, TL08xxC, and TL08xI

 $V_{CC\pm} = \pm 15 \text{ V}$ (unless otherwise noted)

PAI	RAMETER	TEST	T _A ⁽¹⁾		1C, TL08 TL084C	32C,		AC, TL0 L084AC			BC, TL0 L084BC			31I, TL08 TL084I	B2I,	UNIT
		CONDITIONS	^	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
			25°C		3	15		3	6		2	3		3	6	
V _{IO}	Input offset voltage	$V_O = 0$, $R_S = 50 \Omega$	Full range			20			7.5			5			9	mV
α_{VIO}	Temperature coefficient of input offset voltage	$V_O = 0$, $R_S = 50 \Omega$	Full range		18			18			18			18		μV/°C
	Input offset		25°C		5	200		5	100		5	100		5	100	pA
I _{IO}	current ⁽²⁾	V _O = 0	Full range			2			2			2			10	nA
	Input bias		25°C		30	400		30	200		30	200		30	200	pA
I _{IB}	current ⁽²⁾	$V_O = 0$	Full range			10			7			7			20	nA
V _{ICR}	Common- mode input voltage range		25°C	±11	–12 to 15		±11	–12 to 15		±11	–12 to 15		±11	–12 to 15		V
	Maximum	$R_L = 10 \text{ k}\Omega$	25°C	±12	±13.5		±12	±13.5		±12	±13.5		±12	±13.5		
V _{OM}	peak output	R _L ≥ 10 kΩ	Full	±12			±12			±12			±12			V
OW	voltage swing	R _L ≥ 2 kΩ	range	±10	±12		±10	±12		±10	±12		±10	±12		
	Large-signal	10.1/	25°C	25	200		50	200		50	200		50	200		
A _{VD}	differential voltage amplification	$V_O = \pm 10 \text{ V},$ $R_L \ge 2 \text{ k}\Omega$	Full range	15			15			25			25			V/mV
B ₁	Unity-gain bandwidth		25°C		3			3			3			3		MHz
r _i	Input resistance		25°C		10 ¹²			10 ¹²			10 ¹²			10 ¹²		Ω
CMRR	Common- mode rejection ratio	$V_{IC} = V_{ICR}min,$ $V_{O} = 0,$ $R_{S} = 50 \Omega$	25°C	70	86		75	86		75	86		75	86		dB
k _{SVR}	Supply- voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	$V_{CC} = \pm 15 \text{ V to}$ $\pm 9 \text{ V,}$ $V_{O} = 0$, $R_{S} = 50 \Omega$	25°C	70	86		80	86		80	86		80	86		dB

⁽¹⁾ All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified. Full range for T_A is 0°C to 70°C for TL08_C, TL08_AC, TL08_BC and -40°C to 85°C for TL08_I.

Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 13. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.



Electrical Characteristics for TL08xC, TL08xxC, and TL08xI (continued)

 $V_{CC\pm} = \pm 15 \text{ V}$ (unless otherwise noted)

PAR	RAMETER	TEST TAG			1C, TL08 TL084C	32C,	TL081AC, TL082AC, TL084AC		TL081BC, TL082BC, TL084BC			TL081I, TL082I, TL084I			UNIT	
		CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
I _{CC}	Supply current (each amplifier)	V _O = 0, No load	25°C		1.4	2.8		1.4	2.8		1.4	2.8		1.4	2.8	mA
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100	25°C		120			120			120			120		dB

6.6 Electrical Characteristics for TL08xM and TL084x

 $V_{CC+} = \pm 15 \text{ V}$ (unless otherwise noted)

		(1)	_	TL0	81M, TL082	:M	TL0	84Q, TL08	4M	
	PARAMETER	TEST CONDITIONS ⁽¹⁾	T _A	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	Innut offeet veltege	V 0.B 50.0	25°C		3	6		3	9	mV
V_{IO}	Input offset voltage	$V_{O} = 0, R_{S} = 50 \Omega$	Full range			9			15	mv
α_{VIO}	Temperature coefficient of input offset voltage	$V_{O} = 0, R_{S} = 50 \Omega$	Full range		18			18		μV/°C
	Input offset current ⁽²⁾		25°C		5	100		5	100	pА
I _{IO}	input onset current	V _O = 0	125°C			20			20	nA
	I = =		25°C		30	200		30	200	pА
I _{IB}	Input bias current ⁽²⁾	V _O = 0	125°C			50			50	nA
V _{ICR}	Common-mode input voltage range		25°C	±11	-12 to 15		±11	-12 to 15		V
		$R_L = 10 \text{ k}\Omega$	25°C	±12	±13.5		±12	±13.5		
V_{OM}	Maximum peak output voltage swing	R _L ≥ 10 kΩ	Full rooms	±12			±12			V
	output voltago ownig	R _L ≥ 2 kΩ	Full range	±10	±12		±10	±12		
^	Large-signal differential	$V_{\Omega} = \pm 10 \text{ V}, R_{I} \ge 2 \text{ k}\Omega$	25°C	25	200		25	200		V/mV
A_{VD}	voltage amplification	$V_0 = \pm 10 \text{ V}, R_L \ge 2 \text{ K}\Omega$	Full range	15			15			V/IIIV
B ₁	Unity-gain bandwidth		25°C		3			3		MHz
r _i	Input resistance		25°C		10 ¹²			10 ¹²		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min,$ $V_O = 0, R_S = 50 \Omega$	25°C	80	86		80	86		dB
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	$V_{CC} = \pm 15 \text{ V to } \pm 9 \text{ V},$ $V_{O} = 0, R_{S} = 50 \Omega$	25°C	80	86		80	86		dB
Icc	Supply current (each amplifier)	V _O = 0, No load	25°C		1.4	2.8		1.4	2.8	mA
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100	25°C		120			120		dB

⁽¹⁾ All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified.

6.7 Operating Characteristics

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		$V_I = 10 \text{ V}, R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF},$ See Figure 19	8 ⁽¹⁾	13		
SR	Slew rate at unity gain	V_I = 10 V, R_L = 2 k Ω , C_L = 100 pF, T_A = - 55°C to 125°C, See Figure 19	5 ⁽¹⁾			V/µs

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

⁽²⁾ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 13. Pulse techniques must be used that maintain the junction temperatures as close to the ambient temperature as possible.



Operating Characteristics (continued)

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
t _r	Rise-time	$V_{I} = 20 \text{ V}, R_{L} = 2 \text{ k}\Omega,$	C _L = 100 pF,		0.05		μs
	overshoot factor	See Figure 19			20%		
V	Equivalent input noise	R _S = 20 Ω	f = 1 kHz		18		nV/√ Hz
V _n	voltage	$R_{S} = 20.12$	f = 10 Hz to 10 kHz		4		μV
In	Equivalent input noise current	$R_S = 20 \Omega$,	f = 1 kHz		0.01		pA/√ Hz
THD	Total harmonic distortion	V_I rms = 6 V, A_{VD} = 1, f = 1 kHz,	$R_S \le 1 \text{ k}\Omega, R_L \ge 2 \text{ k}\Omega,$		0.003%		

6.8 Dissipation Rating Table

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D (14 pin)	680 mW	7.6 mW/°C	60°C	604 m/W	490 mW	186 mW
FK	680 mW	11.0 mW/°C	88°C	680 m/W	680 mW	273 mW
J	680 mW	11.0 mW/°C	88°C	680 m/W	680 mW	273 mW
JG	680 mW	8.4 mW/°C	69°C	672 m/W	546 mW	210 mW

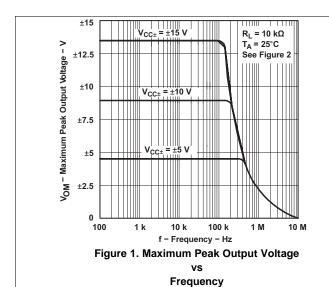


6.9 Typical Characteristics

Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices. The Figure numbers referenced in the following graphs are located in *Parameter Measurement Information*.

Table 1. Table of Graphs

			Figure
V _{OM}	Maximum peak output voltage	versus Frequency versus Free-air temperature versus Load resistance versus Supply voltage	Figure 1, Figure 2, Figure 3 Figure 4 Figure 5 Figure 6
٨	Large-signal differential voltage amplification	versus Free-air temperature versus Load resistance	Figure 7 Figure 8
A _{VD}	Differential voltage amplification	versus Frequency with feed-forward compensation	Figure 9
P _D	Total power dissipation	versus Free-air temperature	Figure 10
I _{CC}	Supply current	versus Free-air temperature versus Supply voltage	Figure 11 Figure 12
I _{IB}	Input bias current	versus Free-air temperature	Figure 13
	Large-signal pulse response	versus Time	Figure 14
Vo	Output voltage	versus Elapsed time	Figure 15
CMRR	Common-mode rejection ratio	versus Free-air temperature	Figure 16
V _n	Equivalent input noise voltage	versus Frequency	Figure 17
THD	Total harmonic distortion	versus Frequency	Figure 18



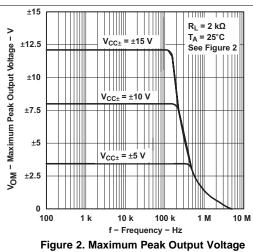
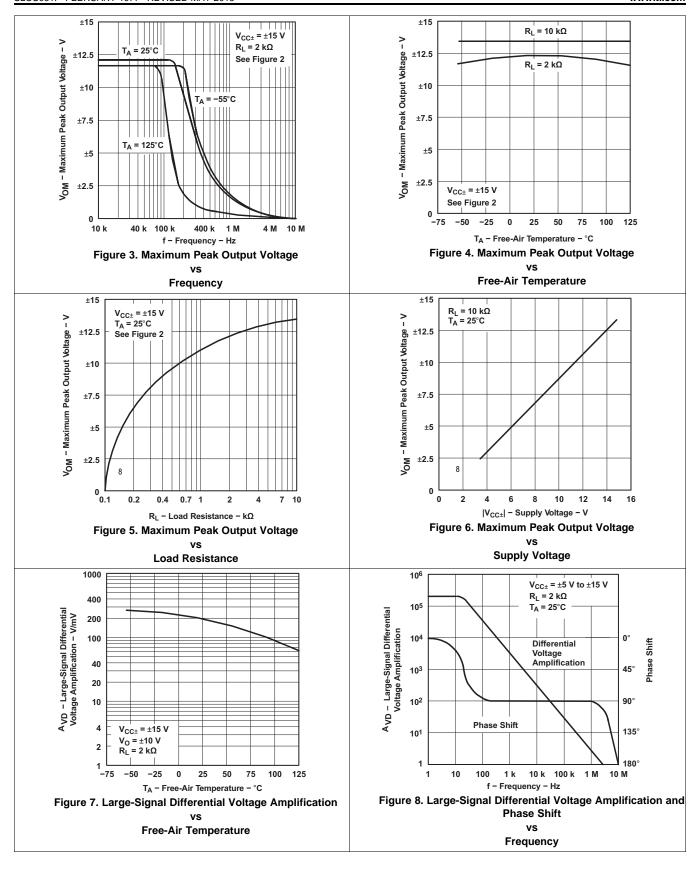
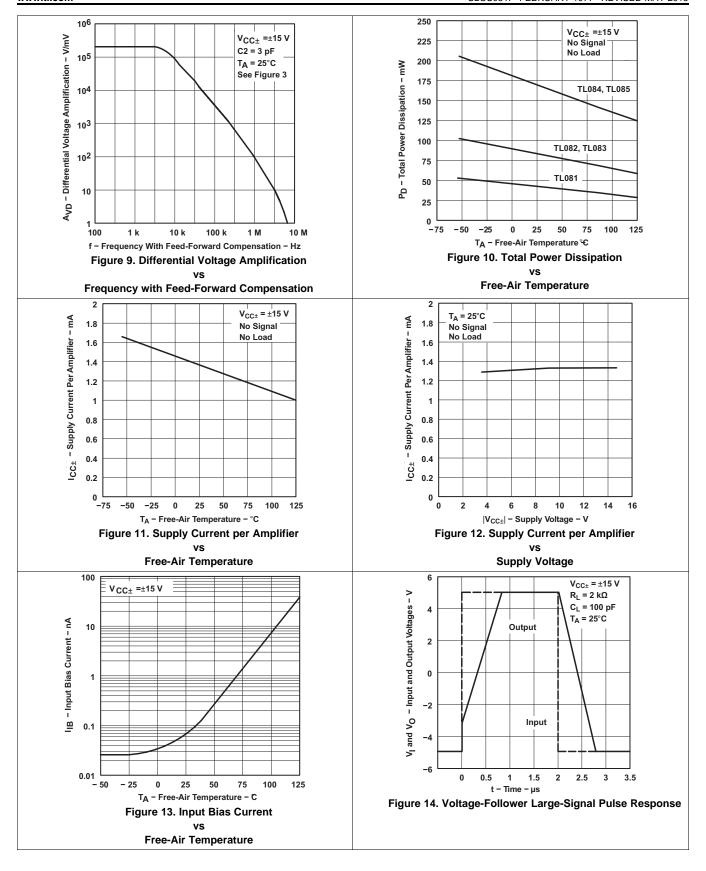


Figure 2. Maximum Peak Output Voltag vs Frequency

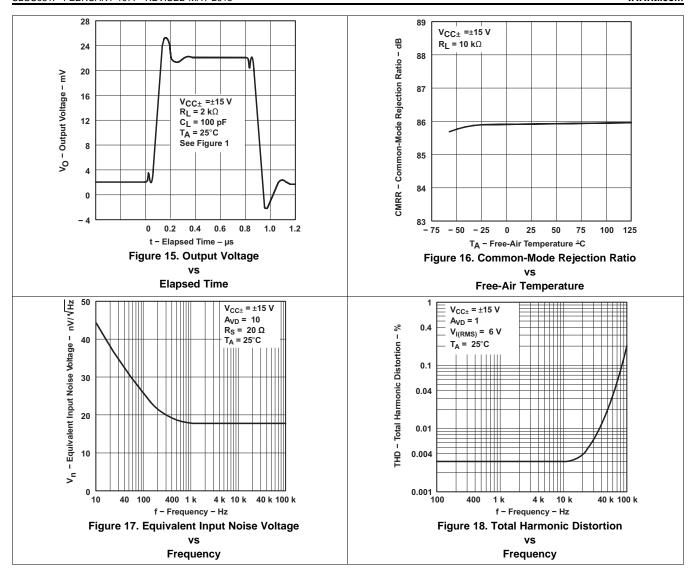














7 Parameter Measurement Information

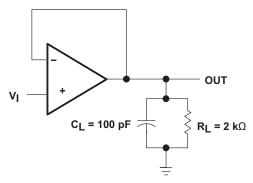


Figure 19. Test Figure 1

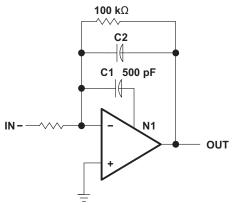


Figure 21. Test Figure 3

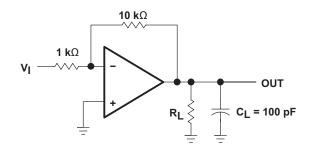


Figure 20. Test Figure 2

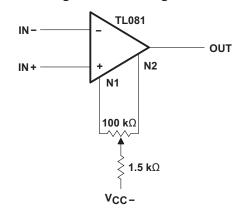


Figure 22. Test Figure 4



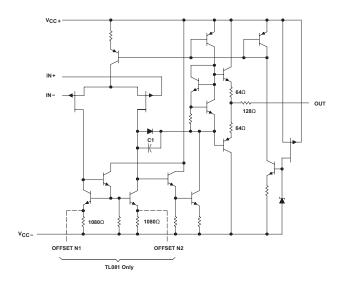
8 Detailed Description

8.1 Overview

The TL08xx JFET-input operational amplifier family is designed to offer a wider selection than any previously developed operational amplifier family. Each of these JFET-input operational amplifiers incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low input bias and offset currents, and low offset-voltage temperature coefficient. Offset adjustment and external compensation options are available within the TL08xx family.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from −40°C to 85°C. The Q-suffix devices are characterized for operation from −40°C to +125°C. The M-suffix devices are characterized for operation over the full military temperature range of −55°C to +125°C.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Total Harmonic Distortion

Harmonic distortions to an audio signal are created by electronic components in a circuit. Total harmonic distortion (THD) is a measure of harmonic distortions accumulated by a signal in an audio system. These devices have a very low THD of 0.003% meaning that the TL08x devices will add little harmonic distortion when used in audio signal applications.

8.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 13-V/µs slew rate.

8.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.



9 Applications and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TL08x series of operational amplifiers can be used in countless applications. The few applications in this section show principles used in all applications of these parts.

9.2 Typical Applications

9.2.1 Inverting Amplifier Application

A typical application for an operational amplifier in an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

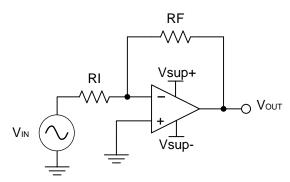


Figure 23. Schematic for Inverting Amplifier Application

9.2.1.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application will scale a signal of ± 0.5 V to ± 1.8 V. Setting the supply at ± 12 V is sufficient to accommodate this application.

9.2.1.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier:

$$A_{v} = \frac{VOUT}{VIN} \tag{1}$$

$$A_v = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

Once the desired gain is determined, choose a value for RI or RF. Choosing a value in the $k\Omega$ range is desirable because the amplifier circuit will use currents in the milliamp range. This ensures the part will not draw too much current. This example will choose 10 $k\Omega$ for RI which means 36 $k\Omega$ will be used for RF. This was determined by Equation 3.

$$A_v = -\frac{RF}{RI} \tag{3}$$

Typical Applications (continued)

9.2.1.3 Application Curve

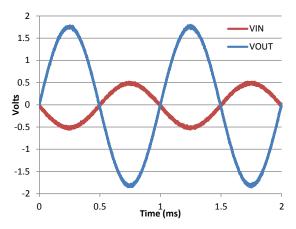


Figure 24. Input and output voltages of the inverting amplifier

9.3 System Examples

9.3.1 General Applications

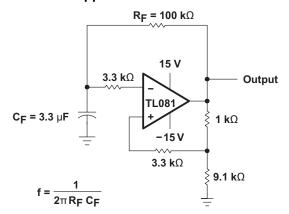


Figure 25. 0.5-Hz Square-Wave Oscillator

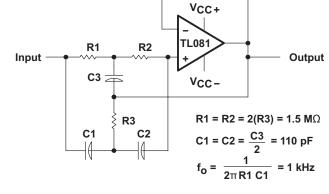


Figure 26. High-Q Notch Filter

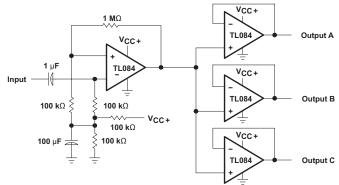
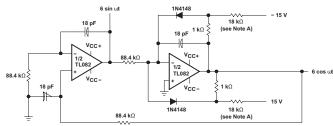


Figure 27. Audio-Distribution Amplifier



A. These resistor values may be adjusted for a symmetrical output.

Figure 28. 100-kHz Quadrature Oscillator



System Examples (continued)

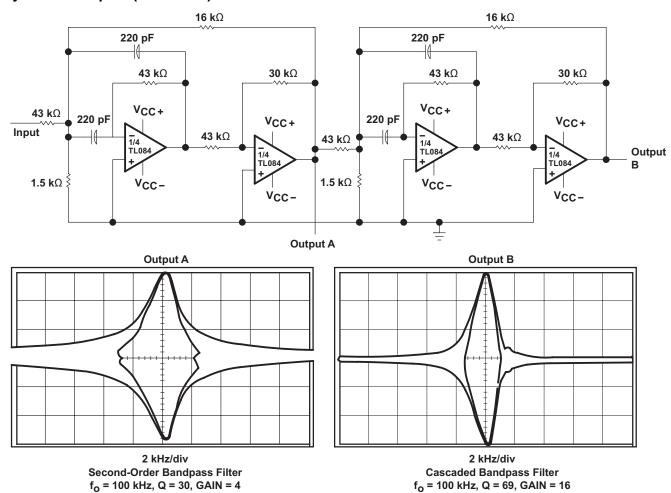


Figure 29. Positive-Feedback Bandpass Filter



10 Power Supply Recommendations

CAUTION

Supply voltages larger than 36 V for a single-supply or outside the range of ± 18 V for a dual-supply can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout*.

11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the
 operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance
 power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds, paying attention to the flow of the ground current. For more detailed information, refer to
 Circuit Board Layout Techniques, (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If
 it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as
 opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting
 input minimizes parasitic capacitance, as shown in Layout Examples.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.



11.2 Layout Examples



Figure 30. Operational Amplifier Board Layout for Noninverting Configuration

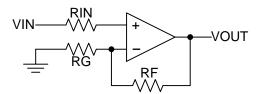


Figure 31. Operational Amplifier Schematic for Noninverting Configuration



Click here

Click here

Click here

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For more information, see the following:

• Circuit Board Layout Techniques, SLOA089.

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

TECHNICAL TOOLS & SUPPORT & **PARTS** PRODUCT FOLDER **SAMPLE & BUY DOCUMENTS SOFTWARE** COMMUNITY TL081 Click here Click here Click here Click here Click here TL081A Click here Click here Click here Click here Click here TL081B Click here Click here Click here Click here Click here TL082 Click here Click here Click here Click here Click here TL082A Click here Click here Click here Click here Click here TL082B Click here Click here Click here Click here Click here

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Table 2. Related Links

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

TL084

TL084A

TL084B

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

Click here

Click here

Click here

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Submit Documentation Feedback





17-Mar-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9851501Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB	Samples
5962-9851501QPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	9851501QPA TL082M	Samples
5962-9851503Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 9851503Q2A TL084 MFKB	Samples
5962-9851503QCA	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB	Samples
TL081ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	081AC	Samples
TL081ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	081AC	Samples
TL081ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081ACP	Samples
TL081ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081ACP	Samples
TL081BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	081BC	Samples
TL081BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	081BC	Samples
TL081BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081BCP	Samples
TL081BCPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081BCP	Samples
TL081CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL081C	Samples
TL081CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL081C	Samples
TL081CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081CP	Samples



Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TL081CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL081CP	Samples
TL081CPSR	ACTIVE	so	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T081	Samples
TL081ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TL081IP	Samples
TL082ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082ACP	Samples
TL082ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082ACP	Samples
TL082ACPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082A	Samples
TL082BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples



Orderable Device	Status	Package Type		Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TL082BCDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082BCP	Samples
TL082BCPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082BCP	Samples
TL082CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082CP	Samples
TL082CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL082CP	Samples
TL082CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples
TL082CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples
TL082CPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples



Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Sample
	(1)				-	(2)	(6)	(3)		(4/5)	
TL082CPWE4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Sampl
TL082CPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Sample
TL082CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Sampl
TL082CPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Sampl
TL082ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Sampl
TL082IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Sampl
TL082IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Sampl
TL082IDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Sampl
TL082IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Samp
TL082IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TL082IP	Samp
TL082IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TL082IP	Samp
TL082IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	Z082	Samp
TL082IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	Z082	Samp
TL082MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB	Samp
TL082MJG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	TL082MJG	Samp
TL082MJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	9851501QPA TL082M	Samp
TL084ACD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samp
TL084ACDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samp





Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TL084ACDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samples
TL084ACDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samples
TL084ACDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samples
TL084ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL084ACN	Samples
TL084ACNSR	ACTIVE	so	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084A	Samples
TL084ACNSRG4	ACTIVE	so	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084A	Samples
TL084BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC	Samples
TL084BCDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC	Samples
TL084BCDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC	Samples
TL084BCDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC	Samples
TL084BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL084BCN	Samples
TL084BCNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL084BCN	Samples
TL084CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples





Orderable Device	Status	Package Type	U	Pins	U	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TL084CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL084CN	Samples
TL084CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TL084CN	Samples
TL084CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084	Samples
TL084CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084	Samples
TL084CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T084	Samples
TL084CPWE4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T084	Samples
TL084CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T084	Samples
TL084CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	T084	Samples
TL084ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TL084IN	Samples
TL084INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TL084IN	Samples
TL084MFK	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	TL084MFK	Samples
TL084MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 9851503Q2A TL084	Samples



PACKAGE OPTION ADDENDUM

17-Mar-2017

Orderable Device	Status	Package Type			_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
										MFKB	
TL084MJ	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	TL084MJ	Samples
TL084MJB	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-9851503QC	Samples
										Α	bumpies
										TL084MJB	
TL084QD	ACTIVE	SOIC	D	14	50	Green (RoHS	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	Samples
						& no Sb/Br)					Samples
TL084QDG4	ACTIVE	SOIC	D	14	50	Green (RoHS	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	C1
						& no Sb/Br)					Samples
TL084QDR	ACTIVE	SOIC	D	14	2500	Green (RoHS	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	C 1
						& no Sb/Br)					Samples
TL084QDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	
. 200 . 45 . 10 .	7.31112	23.0	_		_500	& no Sb/Br)	22 5/10	20.0 2000 01121111	.5 .5 120	. 200 . 4	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.





17-Mar-2017

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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OTHER QUALIFIED VERSIONS OF TL082, TL082M, TL084, TL084M:

Catalog: TL082, TL084

Automotive: TL082-Q1, TL082-Q1

• Military: TL082M, TL084M

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 14-Mar-2016

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



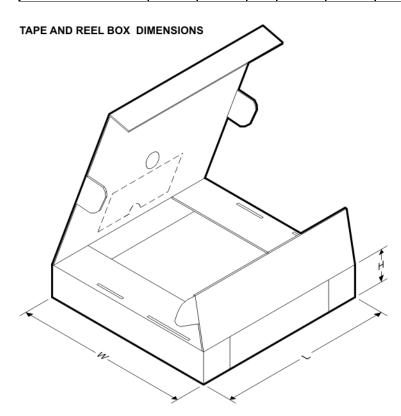
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL081ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TL081IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TL082BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TL082CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL082IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL084ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 14-Mar-2016

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL084ACNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TL084BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TL084IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084QDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084QDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL081ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081BCDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081CPSR	SO	PS	8	2000	367.0	367.0	38.0
TL081IDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082ACDR	SOIC	D	8	2500	367.0	367.0	35.0
TL082ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082ACPSR	SO	PS	8	2000	367.0	367.0	38.0



PACKAGE MATERIALS INFORMATION

www.ti.com 14-Mar-2016

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL082BCDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082CDR	SOIC	D	8	2500	367.0	367.0	35.0
TL082CPSR	SO	PS	8	2000	367.0	367.0	38.0
TL082CPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
TL082IDR	SOIC	D	8	2500	367.0	367.0	35.0
TL082IDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082IPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
TL084ACDR	SOIC	D	14	2500	367.0	367.0	38.0
TL084ACDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084ACNSR	SO	NS	14	2000	367.0	367.0	38.0
TL084BCDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084CDR	SOIC	D	14	2500	367.0	367.0	38.0
TL084CDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084CDRG4	SOIC	D	14	2500	333.2	345.9	28.6
TL084CPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
TL084IDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084QDR	SOIC	D	14	2500	367.0	367.0	38.0
TL084QDRG4	SOIC	D	14	2500	367.0	367.0	38.0

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE

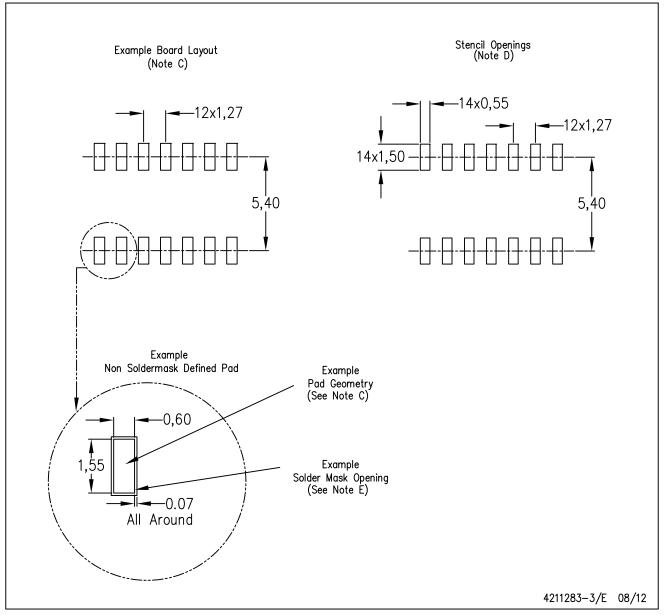


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

